# **General Purpose Transistors**

# **PNP Silicon**

#### Features

• Pb-Free Packages are Available\*

# MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector – Emitter Voltage	V <sub>CEO</sub>	40	Vdc
Collector – Base Voltage	V <sub>CBO</sub>	40	Vdc
Emitter – Base Voltage	V <sub>EBO</sub>	5.0	Vdc
Collector Current – Continuous	Ι <sub>C</sub>	200	mAdc
Total Device Dissipation @ T <sub>A</sub> = 25°C Derate above 25°C	P <sub>D</sub>	625 5.0	mW mW/°C
Total Power Dissipation @ $T_A = 60^{\circ}C$	PD	250	mW
Total Device Dissipation @ T <sub>C</sub> = 25°C Derate above 25°C	P <sub>D</sub>	1.5 12	W mW/°C
Operating and Storage Junction Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	-55 to +150	°C

#### THERMAL CHARACTERISTICS (Note 1)

Characteristic	Symbol	Мах	Unit
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	200	°C/W
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	83.3	°C/W

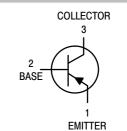
Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

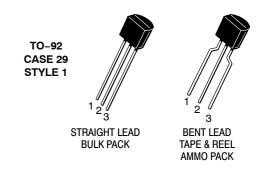
1. Indicates Data in addition to JEDEC Requirements.



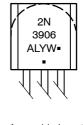
# **ON Semiconductor®**

http://onsemi.com





#### MARKING DIAGRAM



A = Assembly Location L = Wafer Lot

Y = Year

W = Work Week

= Pb-Free Package

(Note: Microdot may be in either location)

# **ORDERING INFORMATION**

See detailed ordering and shipping information in the package dimensions section on page 3 of this data sheet.

\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

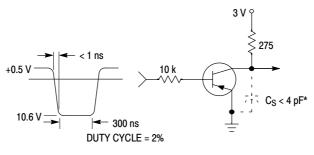
# **ELECTRICAL CHARACTERISTICS** ( $T_A = 25^{\circ}C$ unless otherwise noted)

Characteristic				Min	Max	Unit
OFF CHARACTERIST	rics					
Collector – Emitter Breakdown Voltage (Note 2) $(I_{C} = 1.0 \text{ mAdc}, I_{B} = 0)$			V <sub>(BR)CEO</sub>	40	-	Vdc
Collector-Base Break	down Voltage	$(I_{C} = 10 \ \mu Adc, I_{E} = 0)$	V <sub>(BR)CBO</sub>	40	-	Vdc
Emitter-Base Breakd	own Voltage	$(I_{E} = 10 \ \mu Adc, \ I_{C} = 0)$	V <sub>(BR)EBO</sub>	5.0	-	Vdc
Base Cutoff Current		(V <sub>CE</sub> = 30 Vdc, V <sub>EB</sub> = 3.0 Vdc)	I <sub>BL</sub>	-	50	nAdc
Collector Cutoff Curre	nt	(V <sub>CE</sub> = 30 Vdc, V <sub>EB</sub> = 3.0 Vdc)	I <sub>CEX</sub>	-	50	nAdc
ON CHARACTERIST	CS (Note 2)					
DC Current Gain			h <sub>FE</sub>	60 80 100 60 30	 300 	_
Collector – Emitter Saturation Voltage		$(I_{C} = 10 \text{ mAdc}, I_{B} = 1.0 \text{ mAdc})$ $(I_{C} = 50 \text{ mAdc}, I_{B} = 5.0 \text{ mAdc})$	V <sub>CE(sat)</sub>		0.25 0.4	Vdc
$ \begin{array}{ll} \text{Base-Emitter Saturation Voltage} & (I_C = 10 \text{ mAdc}, I_B = 1.0 \text{ mAdc}) \\ & (I_C = 50 \text{ mAdc}, I_B = 5.0 \text{ mAdc}) \end{array} $		V <sub>BE(sat)</sub>	0.65 -	0.85 0.95	Vdc	
SMALL-SIGNAL CH	ARACTERISTICS					
Current-Gain - Band	width Product	$(I_{C} = 10 \text{ mAdc}, V_{CE} = 20 \text{ Vdc}, f = 100 \text{ MHz})$	f <sub>T</sub>	250	-	MHz
Output Capacitance		(V <sub>CB</sub> = 5.0 Vdc, I <sub>E</sub> = 0, f = 1.0 MHz)	C <sub>obo</sub>	-	4.5	pF
Input Capacitance		$(V_{EB} = 0.5 \text{ Vdc}, I_C = 0, f = 1.0 \text{ MHz})$	C <sub>ibo</sub>	-	10	pF
Input Impedance (I		(I <sub>C</sub> = 1.0 mAdc, V <sub>CE</sub> = 10 Vdc, f = 1.0 kHz)	h <sub>ie</sub>	2.0	12	kΩ
Voltage Feedback Rat	tio	(I <sub>C</sub> = 1.0 mAdc, V <sub>CE</sub> = 10 Vdc, f = 1.0 kHz)	h <sub>re</sub>	0.1	10	X 10 <sup>-4</sup>
Small-Signal Current	Gain	(I <sub>C</sub> = 1.0 mAdc, V <sub>CE</sub> = 10 Vdc, f = 1.0 kHz)	h <sub>fe</sub>	100	400	-
Output Admittance		(I <sub>C</sub> = 1.0 mAdc, V <sub>CE</sub> = 10 Vdc, f = 1.0 kHz)	h <sub>oe</sub>	3.0	60	μmhos
Noise Figure (I <sub>C</sub> = 100 $\mu$ Adc, V <sub>CE</sub> = 5.0 Vdc, R <sub>S</sub> = 1.0 kΩ, f = 1.0 kH		uAdc, V <sub>CE</sub> = 5.0 Vdc, R <sub>S</sub> = 1.0 kΩ, f = 1.0 kHz)	NF	-	4.0	dB
SWITCHING CHARA	CTERISTICS					
Delay Time	(V <sub>CC</sub> = 3.0 Vdc,	V <sub>BE</sub> = 0.5 Vdc,	t <sub>d</sub>	-	35	ns
Rise Time	$I_{\rm C}$ = 10 mAdc, $I_{\rm E}$		t <sub>r</sub>	-	35	ns
Storage Time	(V <sub>CC</sub> = 3.0 Vdc,	$I_{\rm C}$ = 10 mAdc, $I_{\rm B1}$ = $I_{\rm B2}$ = 1.0 mAdc)	t <sub>s</sub>	-	225	ns
Fall Time	(V <sub>CC</sub> = 3.0 Vdc, I <sub>C</sub> = 10 mAdc, I <sub>B1</sub> = I <sub>B2</sub> = 1.0 mAdc)		t <sub>f</sub>	-	75	ns

#### **ORDERING INFORMATION**

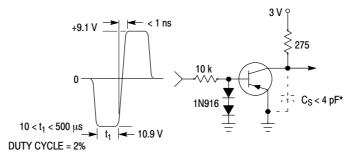
Device	Package	Shipping <sup>†</sup>	
2N3906	TO-92	5000 Units / Bulk	
2N3906G	TO-92 (Pb-Free)	5000 Units / Bulk	
2N3906RL1	TO-92	2000 / Tape & Reel	
2N3906RL1G	TO-92 (Pb-Free)	2000 / Tape & Reel	
2N3906RLRA	TO-92	2000 / Tape & Reel	
2N3906RLRAG	TO-92 (Pb-Free)	2000 / Tape & Reel	
2N3906RLRM	TO-92	2000 / Tape & Ammo Box	
2N3906RLRMG	TO-92 (Pb-Free)	2000 / Tape & Ammo Box	
2N3906RLRP	TO-92	2000 / Tape & Ammo Box	
2N3906RLRPG	TO-92 (Pb-Free)	2000 / Tape & Ammo Box	

+For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.



\* Total shunt capacitance of test jig and connectors

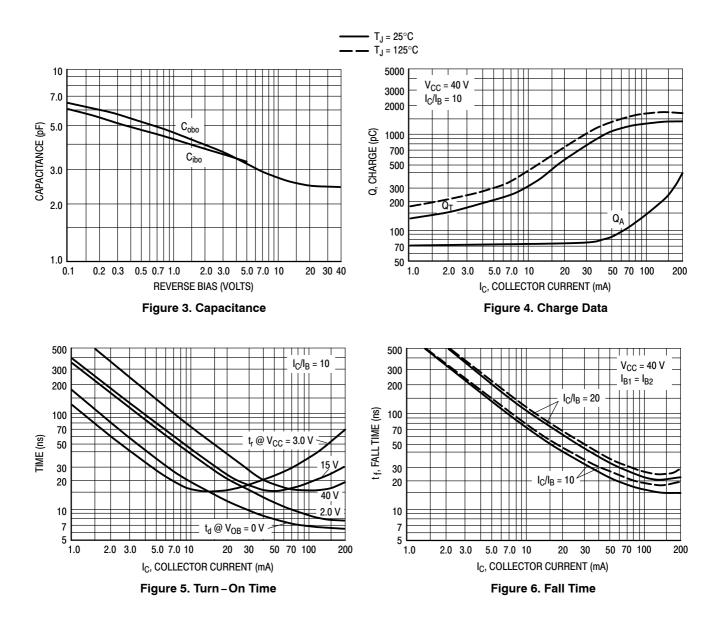
## Figure 1. Delay and Rise Time Equivalent Test Circuit



\* Total shunt capacitance of test jig and connectors

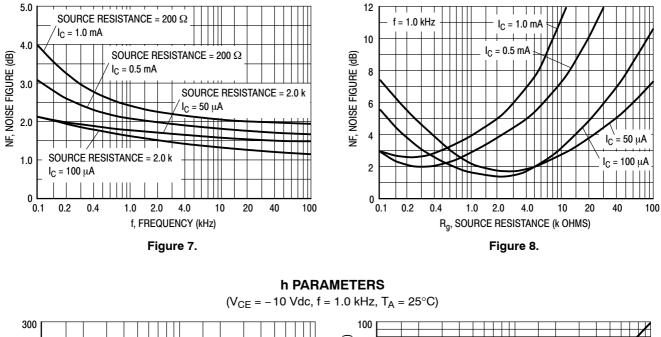
Figure 2. Storage and Fall Time Equivalent Test Circuit

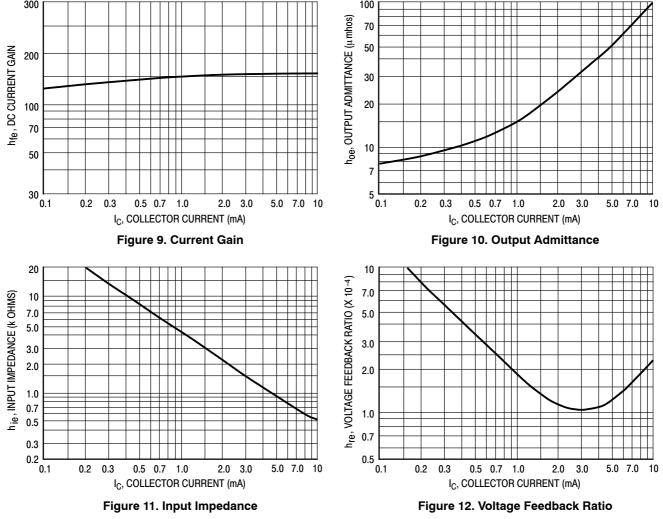
# **TYPICAL TRANSIENT CHARACTERISTICS**



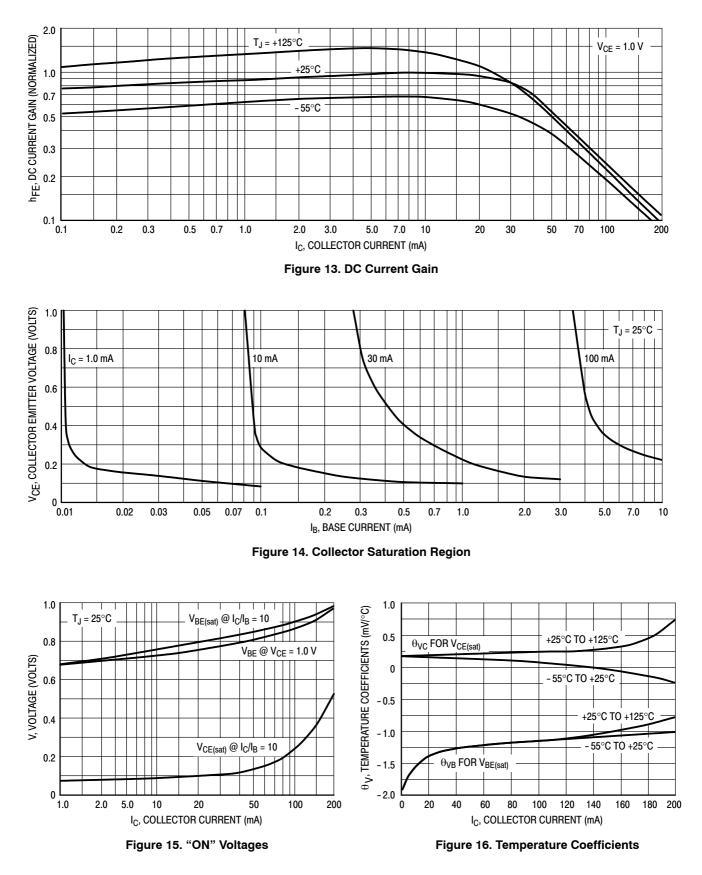
## TYPICAL AUDIO SMALL-SIGNAL CHARACTERISTICS NOISE FIGURE VARIATIONS

(V<sub>CE</sub> = -5.0 Vdc, T<sub>A</sub> =  $25^{\circ}$ C, Bandwidth = 1.0 Hz)

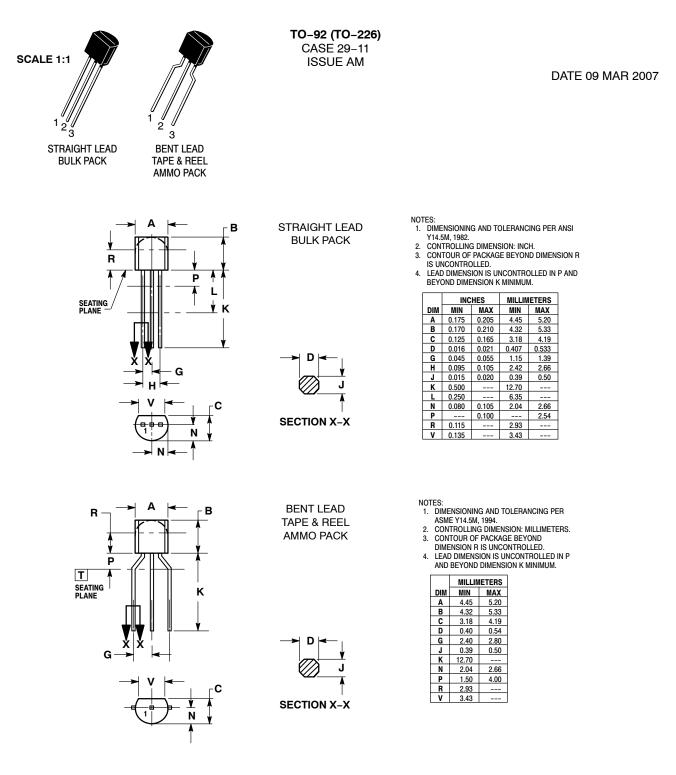




# **TYPICAL STATIC CHARACTERISTICS**



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## **STYLES ON PAGE 2**

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#### TO-92 (TO-226) CASE 29-11 **ISSUE AM**

STYLE 3: PIN 1. ANODE

#### DATE 09 MAR 2007

	EMITTER BASE COLLECTOR
STYLE 6: PIN 1. 2. 3.	SOURCE & SUBSTRATE
2.	ANODE CATHODE & ANODE CATHODE
2.	ANODE GATE CATHODE
2.	COLLECTOR EMITTER BASE
STYLE 26: PIN 1. 2. 3.	V <sub>CC</sub> GROUND 2

	BASE EMITTER COLLECTOR
2.	SOURCE DRAIN GATE
2.	MAIN TERMINAL 1 Gate Main Terminal 2
2.	COLLECTOR BASE EMITTER
2.	SOURCE GATE DRAIN
STYLE 32: PIN 1.	BASE

2. COLLECTOR 3. EMITTER

	ANODE ANODE CATHODE
2.	DRAIN GATE SOURCE & SUBSTRATE
2.	3: ANODE 1 GATE CATHODE 2
2.	B: ANODE CATHODE NOT CONNECTED
2.	3: GATE SOURCE DRAIN
STYLE 2	B:

PIN 1. CATHODE ANODE
GATE

STYLE 33: PIN 1. RETURN 2. INPUT 3. OUTPUT

2.	CATHODE CATHODE ANODE
2.	BASE 1 EMITTER BASE 2
2.	EMITTER COLLECTOR BASE
2.	EMITTER COLLECTOR/ANODE CATHODE
2.	NOT CONNECTED ANODE CATHODE
2.	INPUT GROUND LOGIC

# STYLE 5: PIN 1. DRAIN 2. SOURCE 3. GATE STYLE 10: PIN 1. CATHODE 2. GATE 3. ANODE STYLE 15: PIN 1. ANODE 1 2. CATHODE 3. ANODE 2 STYLE 20: PIN 1. NOT CONNECTED 2. CATHODE 3. ANODE STYLE 25: PIN 1. MT 1 2. GATE 3. MT 2 STYLE 30: PIN 1. DRAIN 2. GATE 3. SOURCE STYLE 35: PIN 1. GATE 2. COLLECTOR

3. EMITTER

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